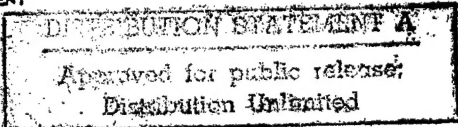


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Workshop Structure

The AHW has a virtually identical meeting structure to the Gordon Conferences which is considered by many to be one of the most productive of all meeting formats. It is a 4 1/2 day meeting with morning and evening sessions and with afternoons free for discussion among participants. The format of the meeting involves several overview presentations and a majority of short, 5 minute presentations of data that can be used as a framework for lively discussions. Each participant is expected to participate in these discussions and are encouraged to bring one or two extra overhead transparencies showing recent data that can be incorporated into the discussions. In the short presentations of data; titles, historical background and summaries are highly discouraged. No poster sessions are planned; everyone will have an opportunity to present their work in the discussion sessions and receive instant feedback. The AHW provides prominent device researchers the opportunity to exchange ideas in a focused format. A summary of the AHW will be published and made available to the attendees and general community.